

### Features:

- Octave bandwidth, specification from 30~3000MHz
- Low noise figure, and high gain, and input PIN limiter protection
- Low VSWR, unconditional stable
- SMA female connector I/O
- Single DC power supply, low power consumption, internal voltage regulator, operating voltage from +10~+15V
- Operating temperature -40~+85°C, storage temperature -55~+125°C

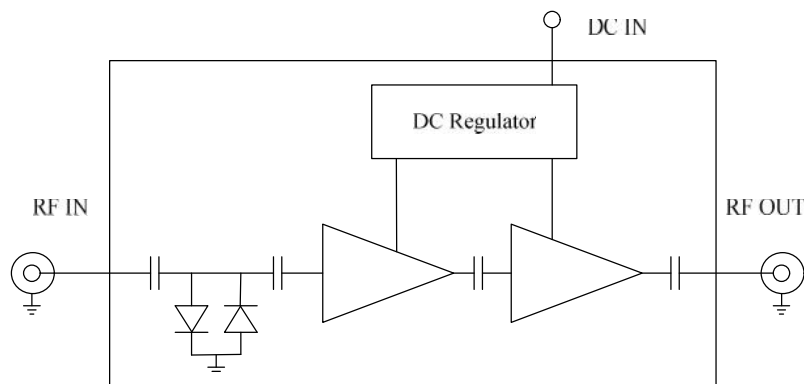
### General Description

ABL0300-01-3017DP is a PIN diode protected two stage enhancement mode pHEMT transistor based broadband low noise amplifier module operating in the frequency range from 30MHz to 3.0GHz. The amplifier provides 30dB of small signal gain with 1.7 dB typical noise figure. The amplifier requires only a single positive DC power supply. Its built-in DC voltage regulator and reverse polarity protection circuitry allows the amplifier to function at different DC supply voltages without affecting the RF performances.

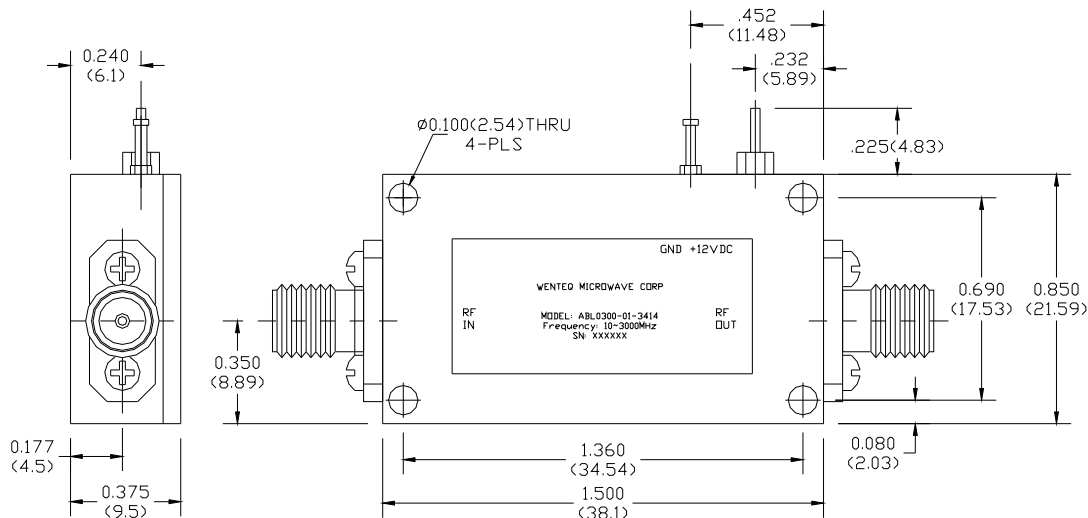
### Electrical Specifications

Parameters	Units	Specifications		
		Minimum	Typical	Maximum
Frequency Range	MHz	30.0		3000.0
Noise Figure @25°C	dB		1.7	2.0
P-1dB Compression Point	dBm	+13.0	+15.0	
Output IP3	dBm	+24.0	+28.0	
Nominal SS Gain @25°C	dB	28.0	30.0	33.0
Gain flatness	dB		+/-0.5	+/-1.0
Gain Variation	dB		+/-1.25	
Input VSWR	-		1.5:1	1.75:1
Output VSWR	-		1.5:1	1.75:1
Reverse Isolation	dB	40.0	45.0	
Spurious	dBc			-70.0
Operating Temperature	°C	-40		+85
Survival Temperature	°C	-55		+125
DC Voltage	°C	+10.0	+12.0	+13.0
DC Supply Current	mA	65.0	80.0	95 mA
In/Out connectors	-	SMA female		
Size	inches	1.5×0.85×0.375		

**Functional Diagram**



**Mechanical Structure:**



Note: All units in inches(mm).

**Housing Material and Surface Finish:**

- Body and cover material: aluminum
- Surface finish: nickel plated
- Connector material: Copper
- Connector surface finish: gold plated

**Absolute Maximum Ratings**

DC Voltage	+15V
RF Input Power	+30dBm
Storage Temperature	-55~+125°C
Operating Temperature	-40~+85°C